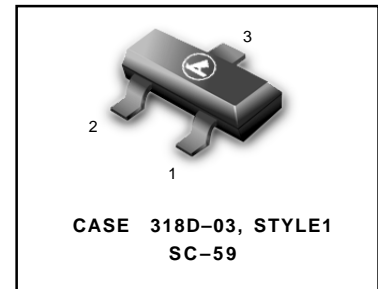
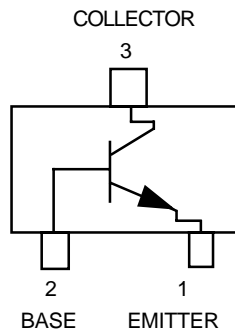


NPN General Purpose Amplifier Transistor Surface Mount

MSD602-RT1



MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	60	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	7.0	Vdc
Collector Current-Continuous	I _C	500	mAdc
Collector Current-Peak	I _{C(P)}	1.0	Adc

THERMAL CHARACTERISTICS

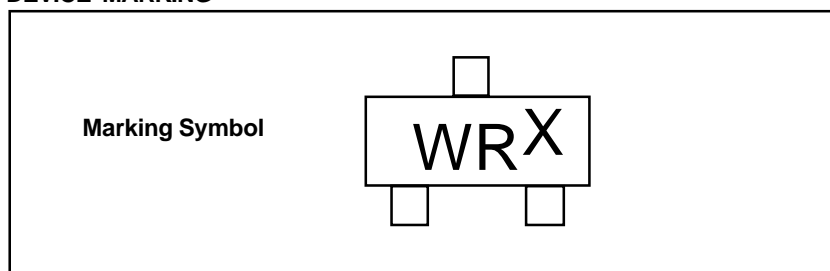
Characteristic	Symbol	Max	Unit
Power Dissipation	P _D	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I _C = 10 mAdc, I _B = 0)	V _{(BR)CEO}	50	—	Vdc
Collector-Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	—	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	7.0	—	Vdc
Collector-Base Cutoff Current (V _{CB} = 20Vdc, I _E = 0)	I _{CBO}	—	0.1	μAdc
DC Current Gain ⁽¹⁾				—
(V _{CE} = 10 Vdc, I _C = 150 mAdc)	h _{FE1}	120	240	
(V _{CE} = 10 Vdc, I _C = 500 mAdc)	h _{FE2}	40	—	
Collector-Emitter Saturation Voltage (I _C = 300 mAdc, I _B = 30 mAdc)	V _{CE(sat)}	—	0.6	Vdc
Output Capacitance (V _{CB} = 10Vdc, I _E = 0, f = 1.0MHz)	C _{cb}	—	15	pF

1. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

DEVICE MARKING



The "X" represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.